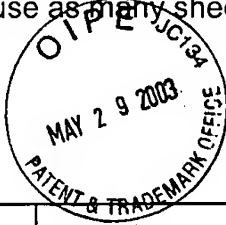



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| | | | | Application Number | 10/073,506 |
| | | | | Filing Date | February 11, 2002 |
| | | | | Confirmation Number | 6190 |
| | | | | First Named Inventor | Robert J. Falster |
| | | | | Group Art Unit | 1775 |
| | | | | Examiner Name | Matthew A. Anderson |
| Sheet | 1 | of | 10 | Attorney Docket No. | MEMC 98-1451/2554.1 |

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| | | | | First Named Inventor | Robert J. Falster |
| | | | | Group Art Unit | 1775 |
| | | | | Examiner Name | Matthew A. Anderson |
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| | | | | First Named Inventor | Robert J. Falster |
| | | | | Group Art Unit | 1775 |
| | | | | Examiner Name | Matthew A. Anderson |
| Sheet | 3 | of | 10 | Attorney Docket No. | MEMC 98-1451/2554.1 |

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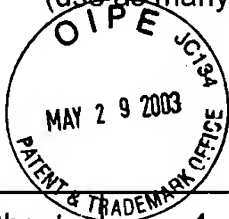
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| First Named Inventor | Robert J. Falster |
| Group Art Unit | 1775 |
| Examiner Name | Matthew A. Anderson |
| Attorney Docket No. | MEMC 98-1451725541 |

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Signature

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 Date
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8/12/03

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| | | | | Filing Date | February 11, 2002 |
| | | | | Confirmation Number | 6190 |
| | | | | First Named Inventor | Robert J. Falster |
| | | | | Group Art Unit | 1775 |
| | | | | Examiner Name | Matthew A. Anderson |
| Sheet | 5 | of | 10 | Attorney Docket No. | MEMC 98-1451/2554.1 |



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| Examiner Signature | <i>Matthew Anderson</i> | Date Considered | 8/12/03 |
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| Filing Date | February 11, 2002 |
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| First Named Inventor | Robert J. Falster |
| Group Art Unit | 1775 |
| Examiner Name | Matthew A. Anderson |
| Attorney Docket No. | MEMC 98-1451/2554.1 |

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| Examiner Initials* | Cite No. ¹ | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published. | T ⁶ |
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Sheet 7 of 10

Attorney Docket No. MEMC 98-1451/2554

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Application Number 10/073,506

Filing Date February 11, 2002

Confirmation Number 6190

First Named Inventor Robert J. Falster

Group Art Unit 1775

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| INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary) | | Application Number | 09/416,998 |
| | | Filing Date | October 13, 1999 |
| | | Confirmation Number | 6867 |
| | | First Named Inventor | Robert J. Falster et al. |
| | | Group Art Unit | 1765 |
| | | Examiner Name | |
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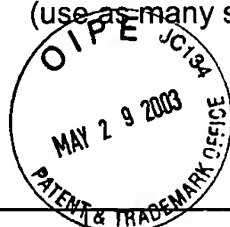
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| INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary) | | Application Number | 09/416,998 |
| | | Filing Date | October 13, 1999 |
| | | Confirmation Number | 6867 |
| | | First Named Inventor | Robert J. Falster et al. |
| | | Group Art Unit | 1765 |
| | | Examiner Name | |
| Sheet 9 of 10 | Attorney Docket No. | MEMC 98-1451 (2554.1) | |



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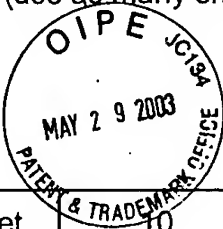
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